Unit: mm

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π-MOSV)

2SK2679

Chopper Regulator, DC-DC Converter and Motor Drive Applications

 $\begin{array}{ll} \bullet & Low\ drain-source\ ON\ resistance & \vdots\ R_{DS}\ (ON) = 0.84\ \Omega\ (typ.) \\ \bullet & High\ forward\ transfer\ admittance & \vdots\ |Y_{fs}| = 4.4\ S\ (typ.) \\ \bullet & Low\ leakage\ current & \vdots\ I_{DSS} = 100\ \mu A\ (max)\ (V_{DS} = 400\ V) \\ \bullet & Enhancement-mode & \vdots\ V_{th} = 2.0 {\sim} 4.0\ V\ (V_{DS} = 10\ V,\ I_{D} = 1\ mA) \\ \end{array}$

Maximum Ratings (Ta = 25°C)

| Characteris | stics | Symbol | Rating | Unit | |
|---------------------------|------------------------|------------------|---------|------|--|
| Drain-source voltage | | V_{DSS} | 400 | V | |
| Drain-gate voltage (Ro | _{SS} = 20 kΩ) | V_{DGR} | 400 | V | |
| Gate-source voltage | | V _{GSS} | ±30 | V | |
| Drain current | DC (Note 1) | I _D | 5.5 | Α | |
| | Pulse (Note 1) | I _{DP} | 22 | Α | |
| Drain power dissipation | n (Tc = 25°C) | P _D | 35 | W | |
| Single pulse avalanche | e energy (Note 2) | E _{AS} | 223 | mJ | |
| Avalanche current | | I _{AR} | 5.5 | Α | |
| Repetitive avalanche e | nergy (Note 3) | E _{AR} | 3.5 | mJ | |
| Channel temperature | | T _{ch} | 150 | °C | |
| Storage temperature range | | T _{stg} | -55~150 | °C | |

Weight: 1.9 g (typ.)

Thermal Characteristics

| Characteristics | Symbol | Max | Unit |
|--|------------------------|------|------|
| Thermal resistance, channel to case | R _{th (ch-c)} | 3.57 | °C/W |
| Thermal resistance, channel to ambient | R _{th (ch-a)} | 62.5 | °C/W |

Note 1: Please use devices on condition that the channel temperature is below 150°C.

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Note 2: V_{DD} = 90 V, T_{ch} = 25°C (initial), L = 12 mH, R_G = 25 Ω , I_{AR} = 5.5 A

Note 3: Repetitive rating: Pulse width limited by maximum channel temperature

This transistor is an electrostatic sensitive device.

Please handle with caution.

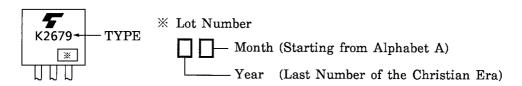
Electrical Characteristics (Ta = 25°C)

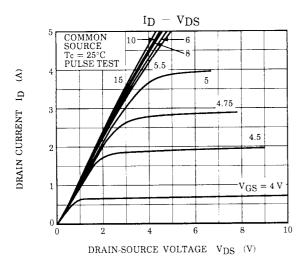
| Charac | teristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|---|-----------------|-----------------------|--|-----|------|-----|------|
| Gate leakage cu | rrent | I _{GSS} | V _{GS} = ±25 V, V _{DS} = 0 V | | _ | ±10 | μΑ |
| Gate-source bre | eakdown voltage | V _(BR) GSS | $I_G = \pm 10 \ \mu A, \ V_{DS} = 0 \ V$ | ±30 | _ | _ | V |
| Drain cut-off cur | rent | I _{DSS} | V _{DS} = 400 V, V _{GS} = 0 V | - | _ | 100 | μΑ |
| Drain-source br | eakdown voltage | V _{(BR)DSS} | I _D = 10 mA, V _{GS} = 0 V | 400 | _ | _ | V |
| Gate threshold v | roltage | V_{th} | V _{DS} = 10 V, I _D = 1 mA | 2.0 | _ | 4.0 | V |
| Drain-source Ol | N resistance | R _{DS} (ON) | V _{GS} = 10 V, I _D = 3 A | _ | 0.84 | 1.2 | Ω |
| Forward transfer | admittance | Y _{fs} | V _{DS} = 10 V, I _D = 3 A | 2.0 | 4.4 | _ | S |
| Input capacitanc | е | C _{iss} | | _ | 720 | _ | pF |
| Reverse transfer | capacitance | C _{rss} | V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz | _ | 80 | _ | |
| Output capacitance | | C _{oss} | | | 250 | _ | |
| Switching time | Rise time | t _r | V_{GS} V_{OV} V_{OU} V_{DD} V_{OU} V_{DD} | _ | 15 | _ | |
| | Turn-on time | t _{on} | | _ | 30 | _ | ne |
| | Fall time | t _f | | ı | 25 | _ | ns |
| | Turn-off time | t _{off} | Duty $\leq 1\%$, $t_W = 10 \mu s$ | - | 110 | _ | |
| Total gate charge (gate-source plus gate-drain) | | Qg | | _ | 17 | | |
| Gate-source charge | | Q _{gs} | $V_{DD} \approx 320 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 5.5 \text{ A}$ | | 10 | _ | nC |
| Gate-drain ("miller") Charge | | Q_{gd} | | | 7 | _ | |

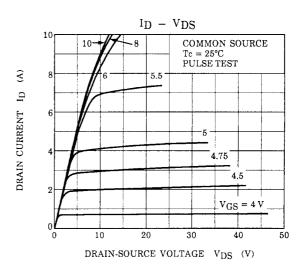
Source-Drain Ratings and Characteristics (Ta = 25°C)

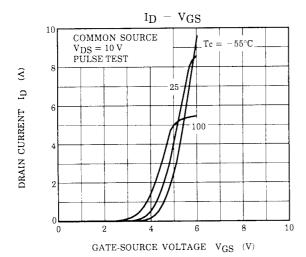
| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|---|------------------|--|-----|------|------|------|
| Continuous drain reverse current (Note 1) | I _{DR} | _ | 1 | - | 5.5 | Α |
| Pulse drain reverse current (Note 1) | I _{DRP} | _ | _ | _ | 22 | Α |
| Forward voltage (diode) | V _{DSF} | I _{DR} = 5.5 A, V _{GS} = 0 V | _ | _ | -1.7 | V |
| Reverse recovery time | t _{rr} | I _{DR} = 5.5 A, V _{GS} = 0 V | | 350 | _ | ns |
| Reverse recovery charge | Q _{rr} | dl _{DR} / dt = 100 Å / μs | 1 | 2.1 | - | μC |

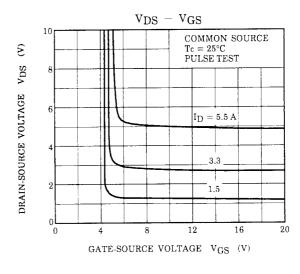
Marking

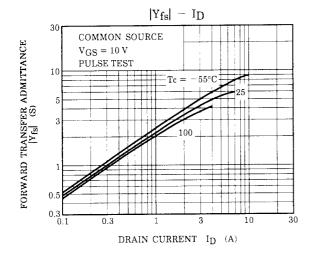


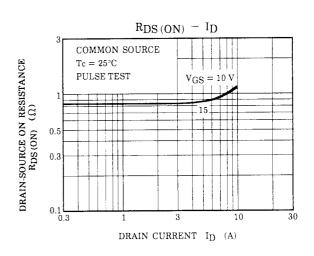




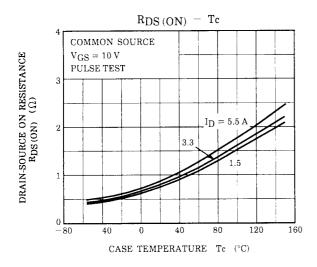


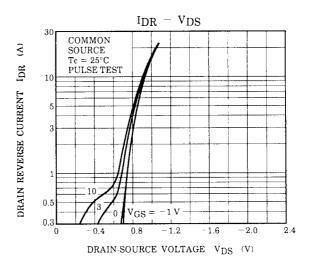


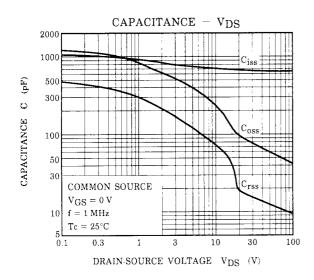


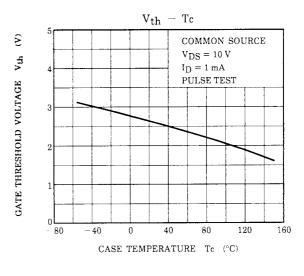


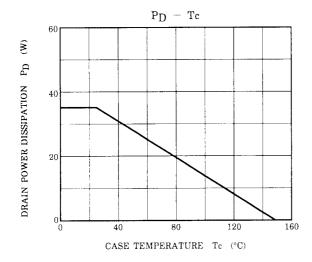
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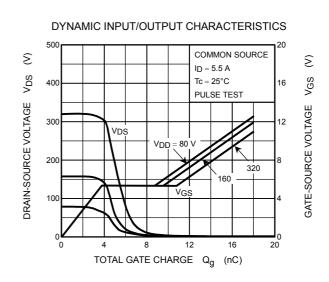




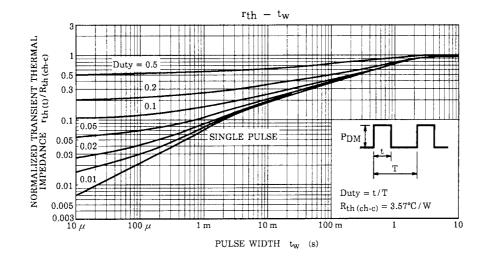


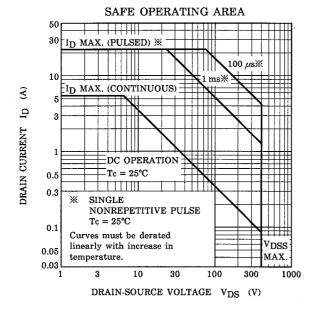


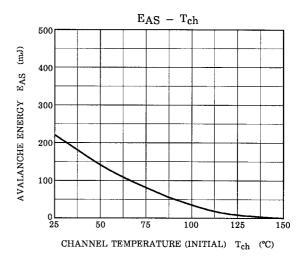


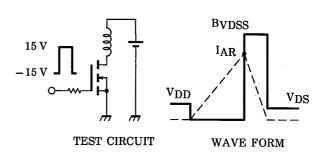


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$$RG = 25 \Omega$$

$$V_{DD} = 90 \text{ V}, L = 12 \text{ mH}$$

$$EAS = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{B_{VDSS}}{B_{VDSS} - V_{DD}}\right)$$

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